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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 5

Complete if Known	
Application Number	10/736,617
Filing Date	December 17, 2003
First Named Inventor	Kristy A. Campbell
Art Unit	~~2825~~ 2829
Examiner Name	~~R. Rocchegiani~~ VY 2/23/2005
Attorney Docket Number	M4065.0698/P698-A

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
VY	**AA	2002/0072188	6/13/2002	Gilton	
	**AB	2002/0106849	08/08/2002	Moore	
	**AC	2002/0123169	09/05/2002	Moore et al.	
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	**AJ	2002/0160551	10//31/2002	Harshfield	
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	**AB1	2003/0128612	07/10/2003	Moore et al.	
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Sheet 2 of 5

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Application Number	10/736,617
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First Named Inventor	Kristy A. Campbell
Art Unit	~~2825~~ 2829
Examiner Name	~~R. Rocchegiani~~ V Vuong
Attorney Docket Number	M4065.0698/P698-A

V4	**AU1	3,988,720	10/1976	Ovshinsky	
	**AV1	4,177,474	12/1979	Ovshinsky	
	**AW1	4,267,261	5/1981	Hallman et al.	
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Sheet	3	of	5

Complete if Known	
Application Number	10/736,617
Filing Date	December 17, 2003
First Named Inventor	Kristy A. Campbell
Art Unit	~~2825~~ 2829
Examiner Name	~~R. Rocchegiani~~
Attorney Docket Number	M4065.0698/P698-A

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Sheet	4	of	5

Complete if Known	
Application Number	10/736,617
Filing Date	December 17, 2003
First Named Inventor	Kristy A. Campbell
Art Unit	~~2825~~ 2829
Examiner Name	~~R. Rocchegiani~~ V Trieu
Attorney Docket Number	M4065.0698/P698-A

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 5 of 5

Complete If Known	
Application Number	10/736,617
Filing Date	December 17, 2003
First Named Inventor	Kristy A. Campbell
Art Unit	~~2825~~ 2829
Examiner Name	~~R. Reechegiani~~
Attorney Docket Number	M4065.0698/P698-A

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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3]-Number[4]-Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
VM	**BA	JP 5-6126916	10/19981	Akira et al.		
VM	**BB	WO 00/48196	08/17/2000	Kozicki et al.		
VM	**BC	WO 02/21542	03/14/2002	Kozicki et al.		

Examiner Signature	V. Reechegiani	Date Considered	03/02/05

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First Named Inventor	Kristy A. Campbell
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Examiner Name	~~Not Yet Assigned~~ V. Yevsikov
Attorney Docket Number	M4065.0698/P698-A

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VV	AV	5,500,532	03/19/1996	Kozicki et al.	

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VV	BA	WO 97/48032	12/18/1997	Kozicki et al.		
VV	BB	WO 99/28914	06/10/1999	Kozicki et al.		

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Application Number	NEW 7
Filing Date	December 12, 2003
First Named Inventor	Kristy A. Campbell
Art Unit	N/A 2829
Examiner Name	~~Not Yet Assigned~~ V. Yevsikov
Attorney Docket Number	M4065.0698/P698-A

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Application Number	NEW
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First Named Inventor	Kristy A. Campbell
Art Unit	~~N/A~~ 2829
Examiner Name	~~Not Yet Assigned~~ V. Yushin
Attorney Docket Number	M4065.0698/P698-A

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First Named Inventor	Kristy A. Campbell
Art Unit	~~N/A~~ 2829
Examiner Name	~~Not Yet Assigned~~ N. Yevsikov
Attorney Docket Number	M4065.0698/P698-A

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Application Number	NEW
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First Named Inventor	Kristy A. Campbell
Art Unit	N/A 2829
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0698/P698-A

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First Named Inventor	Kristy A. Campbell
Art Unit	N/A 2824
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0698/P698-A

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Art Unit	~~N/A~~ 2829
Examiner Name	~~Not Yet Assigned~~ V. Yoodi Rao
Attorney Docket Number	M4065.0698/P698-A

V.4	CL4	Nang, T.T.; Okuda, M.; Matsushita, T.; Yokota, S.; Suzuki, A., Electrical and optical parameters of GexSe1-x amorphous thin films, Jap. J. App. Phys. 15 (1976) 849-853.	
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